

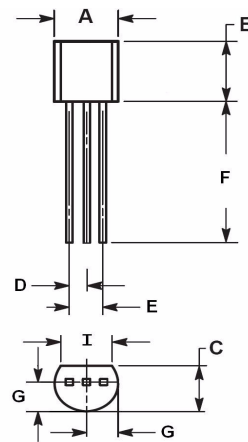
**Sensitive Gate
Silicon Controlled Rectifiers
Reverse Blocking Thyristors**

**SCRs
0.8 AMPERES RMS
600 VOLTS**

FEATURES

- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 Volts
- On- State Current Rating of 0.8 Amperes RMS at 80°C
- High Surge Current Capability — 10 Amperes
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dV/dt — 20 V/us Minimum at Tj=110°C
- Glass-Passivated Surface for Reliability and Uniformity
- Pb-Free Package

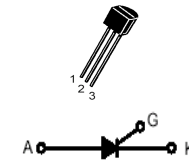
TO-92 (TO-226AA)



TO-92		
DIM.	MIN.	MAX.
A	4.45	4.70
B	4.32	5.33
C	3.18	4.19
D	1.15	1.39
E	2.42	2.66
F	12.7	-----
G	2.04	2.66
I	3.43	-----

All Dimensions in millimeter

PIN ASSIGNMENT	
1	Cathode
2	Gate
3	Anode



MAXIMUM RATINGS (Tj= 25°C unless otherwise noticed)

Rating	Symbol	Value	Unit
Peak Repetitive Off- State Voltage (Tj= -40 to 110°C, Sine Wave, 50 to 60 Hz; Gate Open) S08U25-600A S08U50-600A S08M02-600A	VDRM, VRRM	600	Volts
On-State RMS Current (Tc = 80°C) 180° Conduction Angles	IT(RMS)	0.8	Amp
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, Tj = 25°C)	ITSM	10	Amps
Circuit Fusing Consideration (t = 8.3 ms)	$\int I^2 t$	0.415	A ² s
Forward Peak Gate Power (TA = 25°C, Pulse Width ≤ 1.0 us)	PGM	0.1	Watt
Forward Average Gate Power (TA = 25°C, t = 8.3 ms)	PG(AV)	0.01	Watt
Forward Peak Gate Current (TA = 25°C, Pulse Width ≤ 1.0 us)	IGM	1.0	Amp
Reverse Peak Gate Voltage (TA = 25°C, Pulse Width ≤ 1.0 ms)	VGRM	5	Volts
Operating Junction Temperature Range @ Rate VRRM and VDRM	Tj	-40 to +110	°C
Storage Temperature Range	Tstg	-40 to +150	°C

Notice: (1) VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance - Junction to Case - Junction to Ambient	RthJC RthJA	75 150	°C/W
Maximum Lead Temperature for Soldering Purposes 1/16" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Unit
-----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Peak Reptitive Forward or Reverse Blocking Current (V _D =Rated V _{DRM} and V _{RRM} ; R _{GK} =1K Ohms)	T _J =25°C	I _{DRM}	----	----	10	uA
	T _J =110°C	I _{RRM}	----	----	100	

ON CHARACTERISTICS

Peak Forward On-State Voltage (I _{TM} = ± 1.6A Peak, Pulse Width ≤ 1.0ms, Duty Cycle ≤ 1%)		V _{TM}	----	----	1.7	Volts	
Gate Trigger Current(V _D = 7.0 Vdc, R _L =100 Ohms) (1)		I _{GT}	S08U25	----	----	25	uA
			S08U50	----	----	50	
			S08M02	----	----	200	
Holding Current(V _D = 7.0 Vdc, Initiating Current = 20mA)	T _J =25°C	I _H	----	----	5	mA	
	T _J =-40°C		----	----	10		
Gate Trigger Voltage(V _D = 7.0 Vdc, R _L =100 Ohms) (1)	T _J =25°C	V _{GT}	----	----	0.8	Volts	
	T _J =-40°C		----	----	1.2		
Latch Current(V _D = 7.0 Vdc, R _L 100 Ohms)	T _J =25°C	I _L	----	----	10	mA	
	T _J =-40°C		----	----	15		

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage (V _D =Rated V _{DRM} , Exponential Waveform, P _{GK} =1K Ohms, T _J =110°C)	dv/dt	20	----	----	V/us
----------------------------------------------------------------------------------------------------------------------------------------------------------------	-------	----	------	------	------

(1) R_{GK} current is not included in measurement

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak on State Voltage
I_H	Holding Current

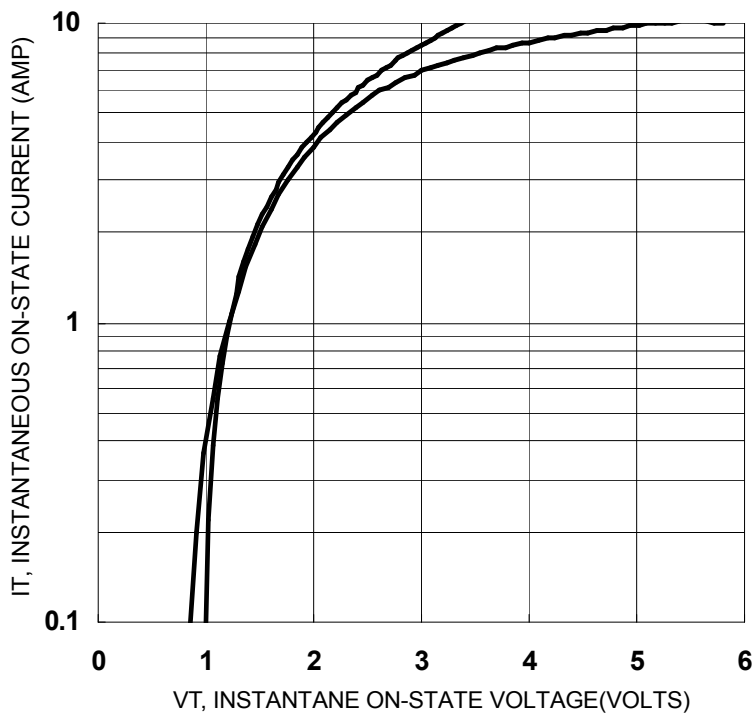
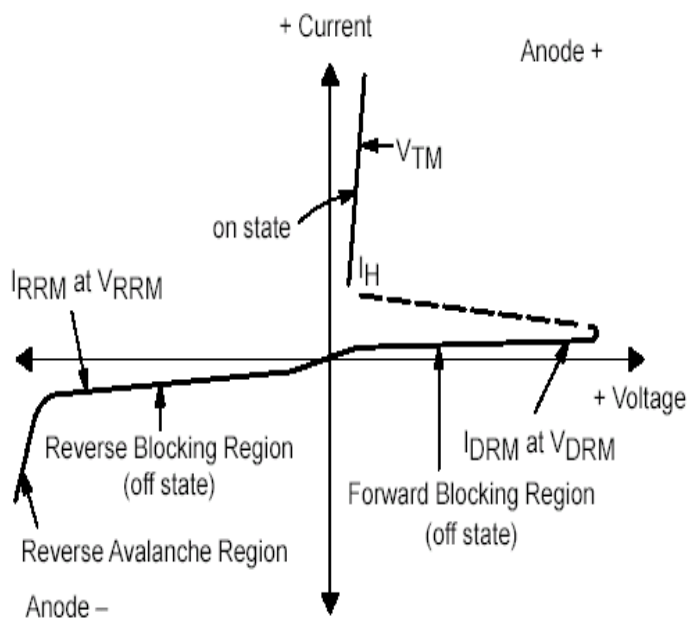


Figure 1. On-State Characteristics

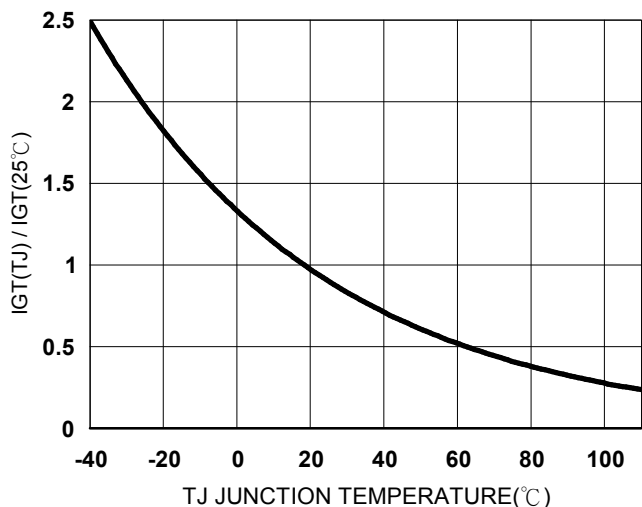


Figure 2. IGT(TJ) / IGT(25°C) versus TJ

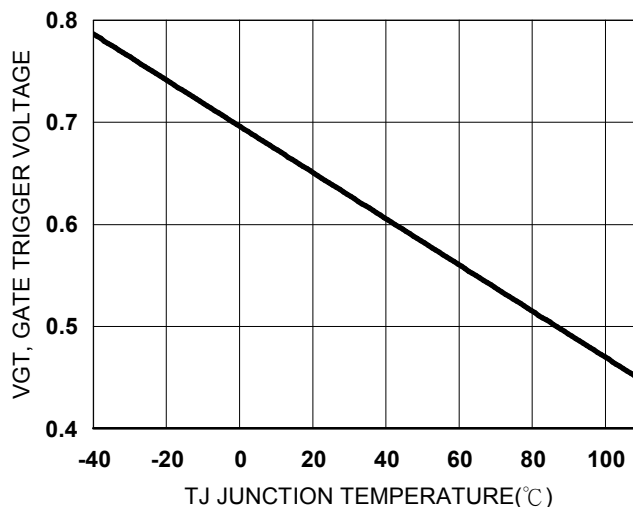


Figure 3. Typical IGT versus TJ

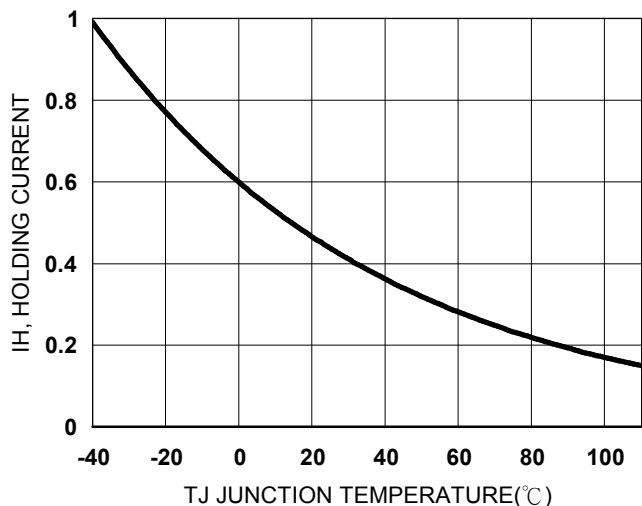


Figure 4. Typical IGH versus TJ

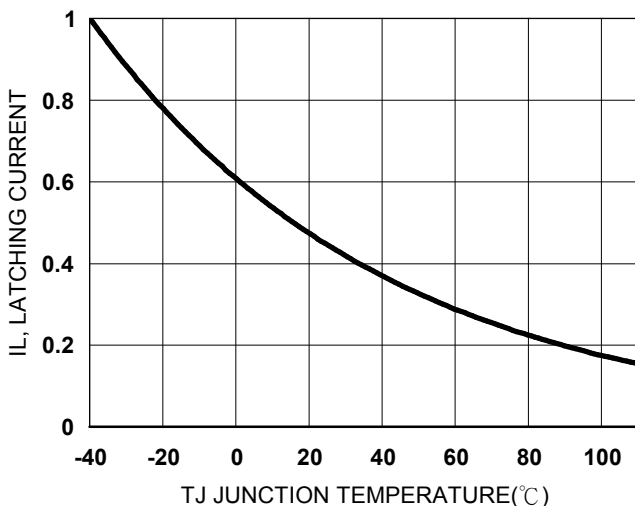


Figure 5. Typical ILL versus TJ

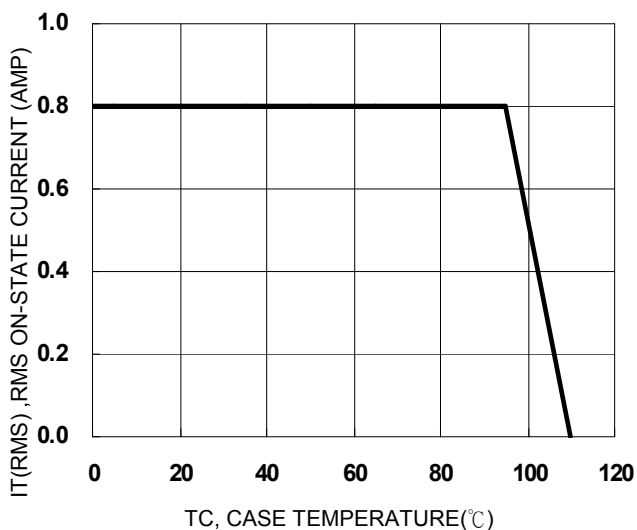


Figure 6. On-State Current Derating Curve

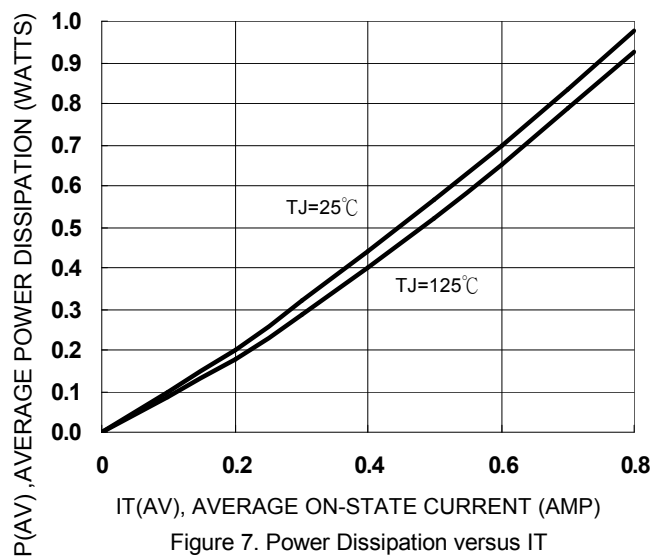


Figure 7. Power Dissipation versus IT

Important Notice and Disclaimer

LSC reserves the right to make changes to this document and its products and specifications at any time without notice. Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

LSC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does LSC assume any liability for application assistance or customer product design. LSC does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of LSC.

LSC products are not authorized for use as critical components in life support devices or systems without express written approval of LSC.